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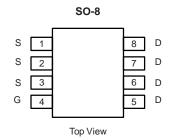
# P-Channel 20-V (D-S) MOSFET

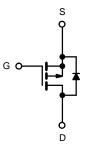
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$ $I_{D}($			
- 20 -	0.042 at V <sub>GS</sub> = - 4.5 V	- 6.6		
	0.054 at V <sub>GS</sub> = - 2.5 V	- 4.4		

### **FEATURES**

- DT-Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC







P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	$\Gamma_A = 25  ^{\circ}\text{C}$ , unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 20		V
Gate-Source Voltage		V <sub>GS</sub>	± 12		V
Continuo Desig Compat /T 450 9C\3	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 6.6	- 4.1	^
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 4.6	- 3.2	
Pulsed Drain Current		I <sub>DM</sub>	- 30		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.3	- 1.1	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.5	1.3	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	] ' <sup>'</sup> D	1.6	0.8	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 t	o 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maniana Landina ta Antina d	t ≤ 10 s	R <sub>thJA</sub>	40	50	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		70	95	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	24	30	

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.



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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$ - 1.0 - 3.0		- 3.0	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	^	
	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			- 5	μA	
On-State Drain Current <sup>b</sup>		V <sub>DS</sub> ≤ - 10V, V <sub>GS</sub> = - 4.5 V	- 20			A	
	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 5				
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.042	0.047	0	
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 4.4 A		0.054	0.060	Ω	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5.8 A		13		S	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 2.3 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.1	V	
Dynamic <sup>a</sup>							
Total Gate Charge	$Q_g$			16	24		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.5 \text{ A}$		2.3		nC	
Gate-Drain Charge	$Q_{gd}$			4.5		1	
Gate Resistance	$R_g$			8.8		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			14	25		
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$		14	25		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		42	70	ns	
Fall Time	t <sub>f</sub>			30	50		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.2 A, dI/dt = 100 A/μs		30	60		

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Guaranteed by design, not subject to production testing.

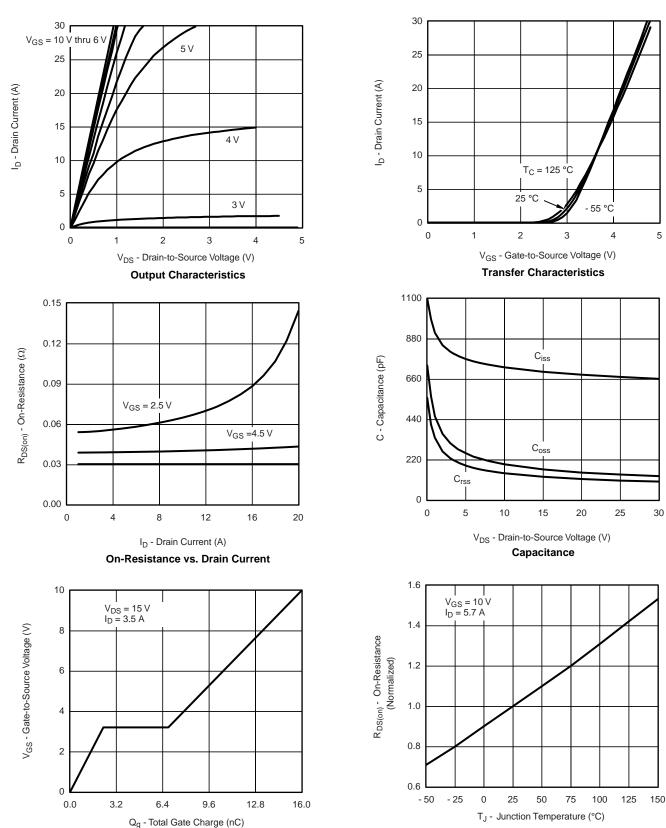
b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 





### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

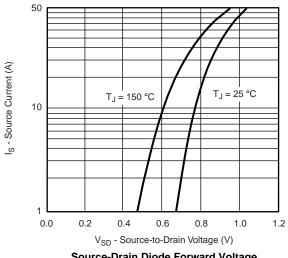
**Gate Charge** 



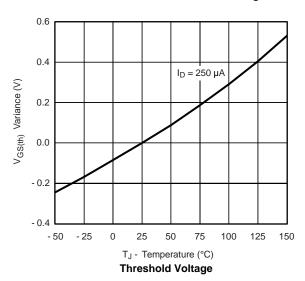
On-Resistance vs. Junction Temperature

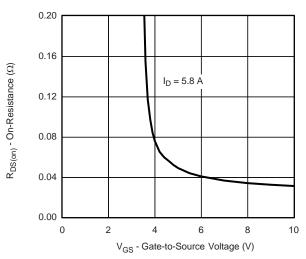


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

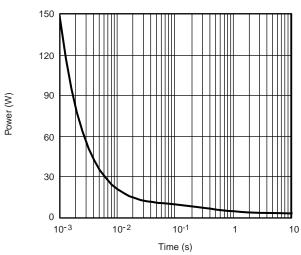


#### Source-Drain Diode Forward Voltage

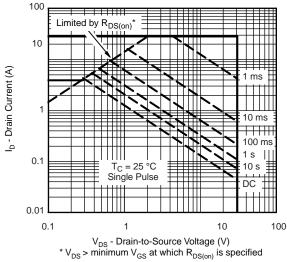




On-Resistance vs. Gate-to-Source Voltage



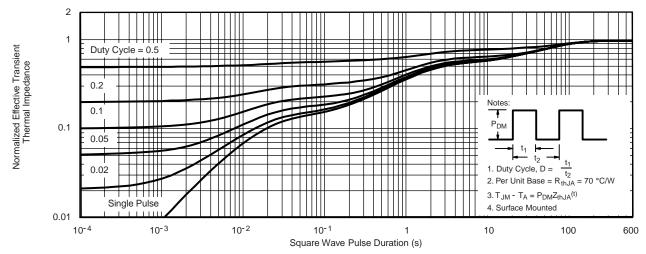
Single Pulse Power, Junction-to-Ambient



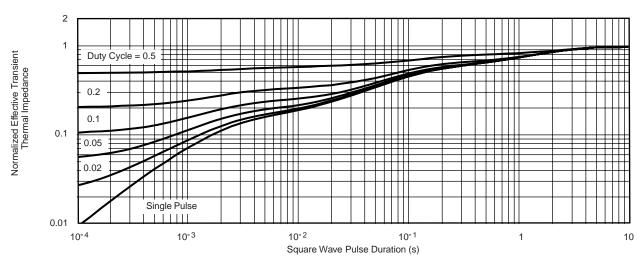
Safe Operating Area, Junction-to-Foot



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot





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